



Docket No. 740756-2324

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of)

Shunpei YAMAZAKI et al)

Serial No. 09/882,265)

Filed: June 18, 2001)

For: SEMICONDUCTOR DEVICE)

Examiner: Thien F. Tran

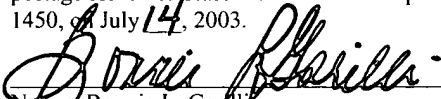
Group Art Unit: 2811

Confirmation No. 7902

RECEIVED
JUL 17 2003
TECHNOLOGY CENTER 2800

Certificate of Mailing

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage for First Class Mail in an envelope addressed to: Commissioner for Patents, P. O. Box 1450, Alexandria, VA 22313-1450, on July 14, 2003.


Name: Bonnie L. Garilli

REQUEST FOR ACKNOWLEDGMENT OF
INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
Alexandria, VA 22313-1450

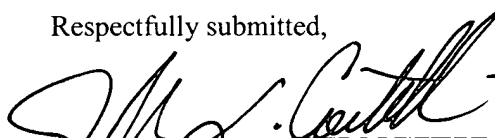
Sir:

An Information Disclosure Statement with Form PTO-1449 was filed in the above-identified patent application on December 20, 2002. Applicants have not yet received back from the Examiner a copy of the Form PTO-1449 initialed to acknowledge the fact that the Examiner has considered the cited disclosed information.

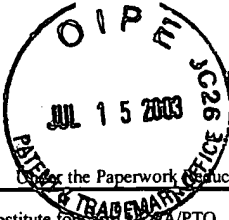
The Examiner is requested to initial and return to the undersigned a copy of the subject Form PTO-1449.

Should there be any questions concerning this communication, please telephone the undersigned at the number set forth below.

Respectfully submitted,


Jeffrey L. Costellia
Registration No. 35,483

Nixon Peabody LLP
8180 Greensboro Drive, Suite 800
McLean, Virginia 22102
(703) 770-9300



Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for PTO/A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
				Application Number	09/882,264
				Filing Date	June 18, 2001
				First Named Inventor	Shunpei YAMAZAKI et al.
				Art Unit	2811
				Examiner Name	Thien Tran
Sheet	1	of	2	Attorney Docket Number	740756-2324

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	U.S. Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
		US-4,766,477	08/23/1998	Nakagawa et al.	
		US-5,162,933	11/10/1992	Kakuda et al.	
		US-5,304,407	04/19/1994	Hayashi et al.	
		US-5,686,980	11/11/1997	Hirayama et al.	
		US-5,932,893	08/03/1999	Miyanaga et al.	
		US-5,943,560	08/24/1999	Chang et al.	
		US-5,977,560	11/02/1999	Banerjee et al.	
		US-6,087,679	07/11/2000	Yamazaki et al.	
		US-6,107,639	08/22/2000	Yamazaki et al.	
		US-6,107,654	08/22/2000	Yamazaki	
		US-6,180,957 B1	01/30/2001	Miyasaka et al.	
		US-6,285,042 B1	09/04/2001	Ohtani et al.	
		US-6,307,214 B1	10/23/2001	Ohtani et al.	
		US-6,307,220 B1	10/23/2001	Yamazaki	
		US-6,335,541 B1	01/01/2002	Ohtani et al.	
		US-6,348,368 B1	02/19/2002	Yamazaki et al.	
		US-2002/0008286 A1	01/24/2002	Yamazaki et al.	
		US-2002/0014625 A1	02/07/2002	Asami et al.	
		US-2002/0038889 A1	04/04/2002	Yamazaki et al.	
		US-2002/0043662 A1	04/18/2002	Yamazaki et al.	

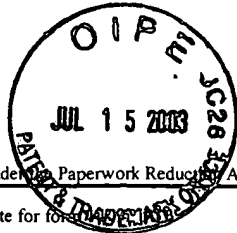
FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ Number ⁴ Kind Code ⁵ (if known)				
		JP 02-219234 A2	08/31/1990	Takaishi		AB
		JP 04-349619 A2	12/04/1992	Hasebe et al.		AB
		JP 11-204434 A2	07/30/1999	Otani et al.		AB
		JP 11-284198 A2	10/15/1999	Yamazaki		AB
		JP 11-307783 A2	11/05/1999	Yamazaki et al.		AB
		JP 11-345767 A2	12/14/1999	Yamazaki et al.		AB
		EP 0 984 317 A2	03/08/2000	Ohtani et al.		FULL
		TW 310478 A	07/11/1997	Chang et al.		AB
		TW 251379 A	07/11/1995	Chang et al.		FULL

Examiner Signature	Date Considered
-----------------------	--------------------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at 222.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, Washington, DC 20231.



Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form PTO/SB/08B INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete if Known	
				Application Number	09/882,264
				Filing Date	June 18, 2001
				First Named Inventor	Shunpei YAMAZAKI et al.
				Group Art Unit	2811
				Examiner Name	Thien F. Tran
Sheet 2 of 2				Attorney Docket Number	740756-2324

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		AM-LCD 99 - July 14-16, 1999 Kogakuin University, Tokyo Japan; "Microtexture Analysis of Location Controlled Large Si Grain Formed by Excimer-Laser Crystallization Method" R. Ishihara et al.; pp.99-102	
		IEEE Electron Device Letters, pp. 160-162; Vol. 17, No. 4, April 1996 "Low Temperature Poly-Si Thin-Film Transistor Fabrication by Metal-Induced Lateral Crystallization" Seok-Woon Lee et al.	

Examiner Signature		Date Considered	
---------------------------	--	------------------------	--

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached.

NVA250348.1